300 mm-Wafer Characterization of Ruthenium Area-Selective Deposition in Nanoscale Line-Space and Hole Patterns

J. J. Clerix[a,b], **A. Delabie**[a,b], **J. Hung**[a,c], **L. Warad**[c], **K. Shah**[c]

[a] *Imec, Kapeldreef 75, 3001 Leuven, Belgium*

[b] *Department of Chemistry, KU Leuven, Celestijnenlaan 200F, 3001 Leuven, Belgium*

[c] *Nova Measuring Instruments*, *3342 Gateway Blvd, Fremont CA 94538, USA*

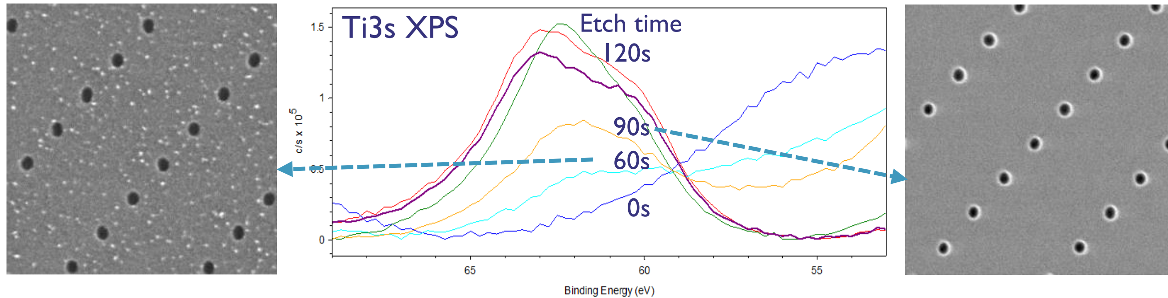

Figure 1. XPS Ti3s signal as function of etch time. At 0s the TiN is covered by Ru. Ru is also etched from SiO_2, which can be seen in the SEM pictures after 60s and 90s etch.

+Author for correspondence: Annelies.Delabie@imec.be

[1] J. Soethoudt et al., Adv. Mater. Interfaces **6**, 1900896 (2019).